

## **isc** Silicon PNP Power Transistor

## 2SA1042

## DESCRIPTION

High Current Capability
Good Linearity of h<sub>FE</sub>
Collector-Emitter Breakdown Voltage-

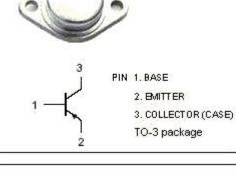
: V<sub>(BR)CEO</sub>= -70V(Min.)

Complement to Type 2SC2432

 Minimum Lot-to-Lot variations for robust device performance and reliable operation

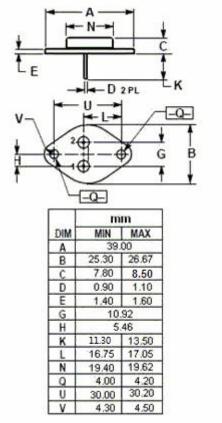
## APPLICATIONS

·Designed for high speed, high voltage switching systems.



## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-70	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-70	0 V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
lc	Collector Current-Continuous	-15	A	
I <sub>B</sub>	Base Current-Continuous	-5	A	
Pc	Collector Power Dissipation $@T_c=25^{\circ}C$	100	W	
Tj	Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature	-65~175	°C	



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## ELECTRICAL CHARACTERISTICS

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA; R <sub>BE</sub> = $\infty$	-70			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -50 μ A; I <sub>E</sub> = 0	-70			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -7A; I <sub>B</sub> = -0.7A			-1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -7A; I <sub>B</sub> = -0.7A			-1.8	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -70V; I <sub>E</sub> = 0			-50	μA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -70V; I <sub>B</sub> = 0			-1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-50	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1.5A; V <sub>CE</sub> = -5V	35		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -15A; V <sub>CE</sub> = -5V	10			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1.0MHz		350		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -10V		60		MHz

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